



Docket No.: R2184.0282
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Hirokazu Iwata et al.

Application No.: 10/765,502

Confirmation No.: 2556

Filed: January 28, 2004

Art Unit: 1722

For: METHOD OF GROWING GROUP III
NITRIDE CRYSTAL, GROUP III NITRIDE
CRYSTAL GROWN THEREBY, GROUP III
NITRIDE CRYSTAL GROWING
APPARATUS AND SEMICONDUCTOR
DEVICE

Examiner: R. Kunemund

AMENDMENT IN RESPONSE TO RESTRICTION REQUIREMENT

MS Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In response to the restriction requirement in the Office Action mailed April 21, 2006, Applicants provisionally elect Group 1, claims 1-14 and 18-25, for continued examination, with traverse.

Amendments to the Claims are reflected in the listing of claims which begins on page 2 of this paper.

Remarks/Arguments begin on page 11 of this paper.